

Schottky Rectifier Diode

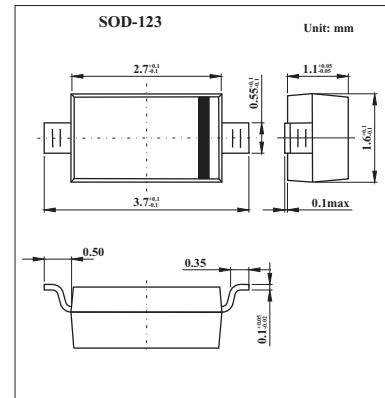
MBR0540

Features

Low forward voltage drop

Guard ring construction for Transient protection.

High conductance.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Peak repetitive peak reverse voltage	V _{RRM}	40	V
Working peak	V _{RWM}		
DC blocking voltage	V _R		
RMS reverse voltage	V _{R(RMS)}	28	V
Average rectified output current	I _O	500	mA
Peak forward surge current	I _{FSM}	5.5	A
Power dissipation	P _d	410	mW
Voltage rate of change	dv/dt	1000	V/μs
Thermal resistance junction to ambient	R _{θJA}	304	°C/W
Storage temperature	T _{stg}	-65 to +125	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{(BR)R}	I _R =20 μA	40			V
Forward voltage	V _F	I _F =0.5A			0.51	V
		I _F =1A			0.62	
Reverse current	I _{R1}	V _R =20V			10	μA
	I _{R2}	V _R =40V			20	μA
Capacitance between terminals	C _T	V _R =0V, f=1MHz			170	pF

Marking

Marking	B4U
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